

# FDMS015N04B N-Channel PowerTrench<sup>®</sup> MOSFET 40V, 100A, 1.5mΩ

# Features

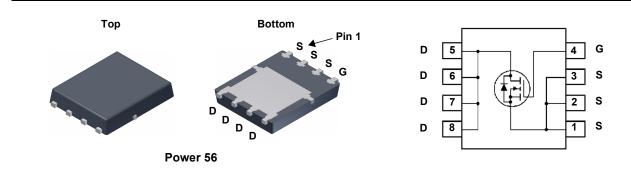
- R<sub>DS(on)</sub> = 1.13mΩ (Typ.)@ V<sub>GS</sub> = 10V, I<sub>D</sub> = 50A
- Advanced Package and Silicon Combination for Low  $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  and High Efficiency
- Fast Switching Speed
- 100% UIL Tested
- · RoHS Compliant

# Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

## Application

- Synchronous Rectification for Server / Telecom PSU
- Battery Charger and Battery Protection circuit
- DC motor drives and Uninterruptible Power Supplies
- Micro Solar Inverter



### MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted\*

Symbol	Parameter			Ratings	Units
V <sub>DSS</sub>	Drain to Source Voltage			40	V
V <sub>GSS</sub>	Gate to Source Voltage			±20	V
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C)	- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C)		٨
		- Continuous (T <sub>A</sub> = 25 <sup>o</sup> C)	(Note 1)	31.3	A
ОМ	Drain Current	- Pulsed	(Note 2)	400	А
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 3)		(Note 3)	526	mJ
P <sub>D</sub>	Rower Dissinction	(T <sub>C</sub> = 25°C)		104	W
	Power Dissipation	(T <sub>A</sub> = 25°C)	(Note 1)	2.5	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C

# **Thermal Characteristics**

Symbol	Parameter	Ratings	Units
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	1.2	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient (Note 1	) 50	0/10

February 2012

Device Marking Device		Packag	e	Reel Size	Таре	e Width		Quantit	y	
		Power 5	56	13 "	12	2 mm		3000 un	its	
Electrica	l Char	acteristics ⊤ <sub>c</sub> =	25 <sup>0</sup> C unless	otherwis	e noted					
Symbol		Parameter		Test Conditions		Min.	Тур.	Max.	Units	
Off Charac	teristic	S								
BV <sub>DSS</sub>	Drain to	to Source Breakdown Voltage		I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V		40	-	-	V	
∆BV <sub>DSS</sub>		kdown Voltage Temperature		$I_D = 250 \mu A$ , Referenced to $25^{\circ}C$		-	37	_	mV/°C	
$\Delta T_{J}$		efficient					-			
I <sub>DSS</sub>		Gate Voltage Drain Current		$V_{DS}$ = 32V, $V_{GS}$ = 0V		-	-	1	μA	
I <sub>GSS</sub>	Gate to	Gate to Body Leakage Current		V <sub>GS</sub> =	±20V, V <sub>DS</sub> = 0V		-	-	±100	nA
On Charac	teristic	S								
V <sub>GS(th)</sub>	Gate T	hreshold Voltage		V <sub>GS</sub> =	V <sub>DS</sub> , I <sub>D</sub> = 250μA		2.0	-	4.0	V
R <sub>DS(on)</sub>	Static D	Drain to Source On Res	sistance	V <sub>GS</sub> =	10V, I <sub>D</sub> = 50A		-	1.13	1.5	mΩ
9 <sub>FS</sub>	Forwar	vard Transconductance		$V_{DS} = 5V, I_D = 50A$		-	171	-	S	
Dynamic (	haract	eristics								
-	c Characteristics						-	6560	8725	۳E
C <sub>iss</sub>		t Capacitance se Transfer Capacitance		V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V f = 1MHz		-	2795	3720	pF pF	
C <sub>oss</sub> C <sub>rss</sub>							162	5720	pF	
C <sub>oss</sub> (er)		Releted Output Capacitance		Vac =	$20V_{00} = 0V_{00}$			3896	_	pF
Q <sub>g(tot)</sub>	• • •	Gate Charge at 10V o Source Gate Charge Charge Threshold to Plateau o Drain "Miller" Charge		$V_{DS} = 20V, V_{GS} = 0V$ $V_{DS} = 20V, I_D = 50A$ $V_{GS} = 0V \text{ to } 10V$ (Note 4)		-	91	118	nC	
$Q_{gs}$						-	26	-	nC	
Q <sub>gs2</sub>						-	9	-	nC	
Q <sub>gd</sub>						-	16	-	nC	
	-	Ŭ				(100 1)				
Switching	1									
t <sub>d(on)</sub>		Turn-On Delay Time		$V_{DD} = 20V, I_D = 50A$ $V_{GS} = 10V, R_{GEN} = 4.7\Omega$		-	34	78	ns	
t <sub>r</sub>						-	24	58	ns	
t <sub>d(off)</sub>		f Delay Time				-	71	152	ns	
t <sub>f</sub>		Off Fall Time		(Note 4) Drain Open, f = 1MHZ		-	26	62	ns	
ESR		ent Series Resistance		Drain G	Spen, I = TMHZ		-	1.4	-	Ω
	1	de Characteristic								
I <sub>S</sub>	Maximum Continuous Drain to Source Dic					-	-	100	A	
I <sub>SM</sub>		aximum Pulsed Drain to Source Diode F				-	-	400	A	
V <sub>SD</sub>		Source Diode Forward	a Voltage	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 50A		-	-	1.3	V	
t <sub>rr</sub>		e Recovery Time			0V, I <sub>SD</sub> = 50A	F	-	78	-	ns
Q <sub>rr</sub>	Reverse	e Recovery Charge		u <sub>F</sub> /at =	= 100A/μs		-	90	-	nC



2. Repetitive Rating: Pulse width limited by maximum junction temperature

4. Essentially Independent of Operating Temperature Typical Characteristics

3. L = 3mH,  $I_{AS}$  = 18.72A, Starting  $T_J$  = 25°C

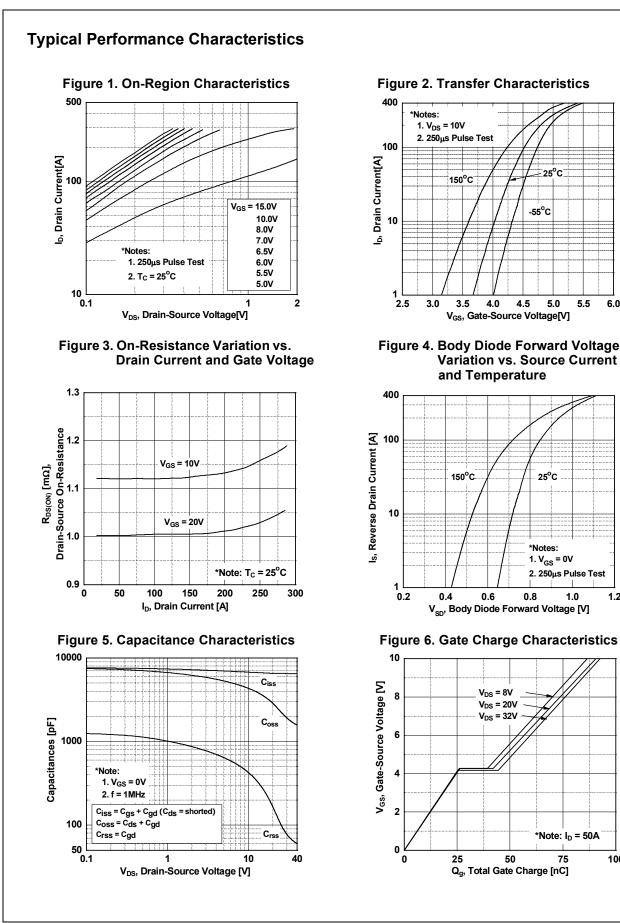
a. 50 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper. b. 125 °C/W when mounted on a minimum pad of 2 oz copper.



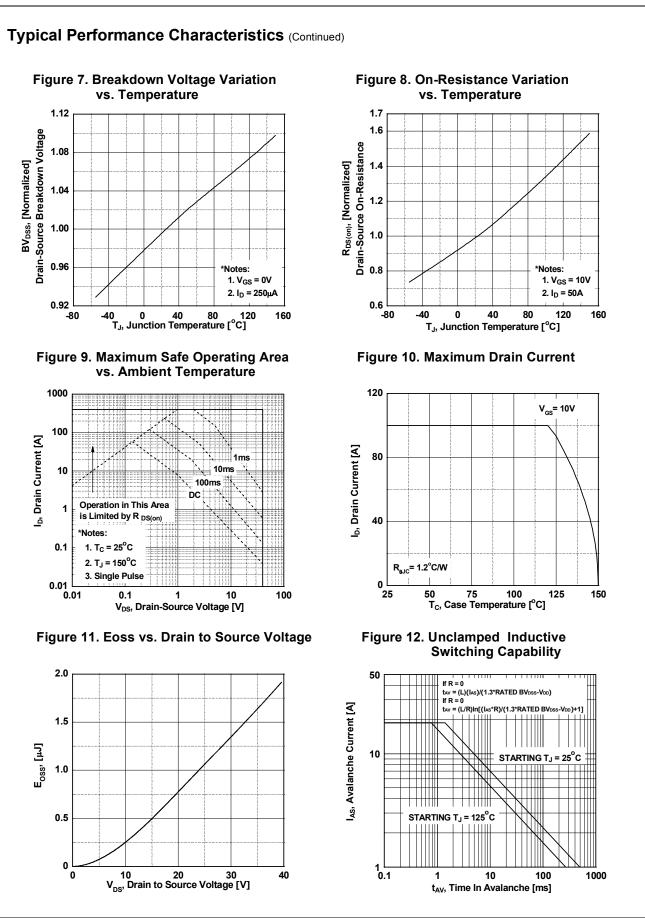
FDMS015N04B N-Channel PowerTrench<sup>®</sup> MOSFET

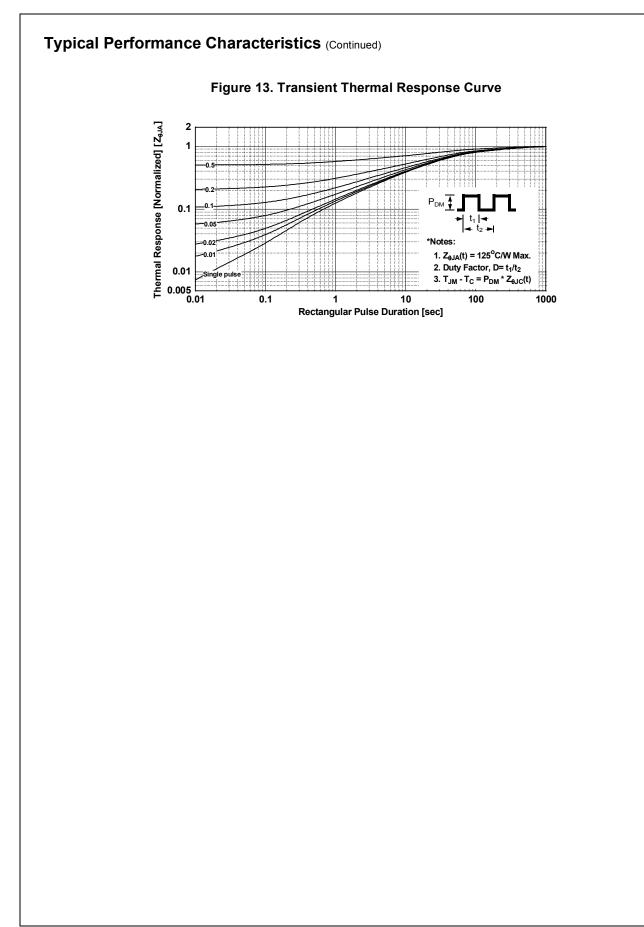
6.0

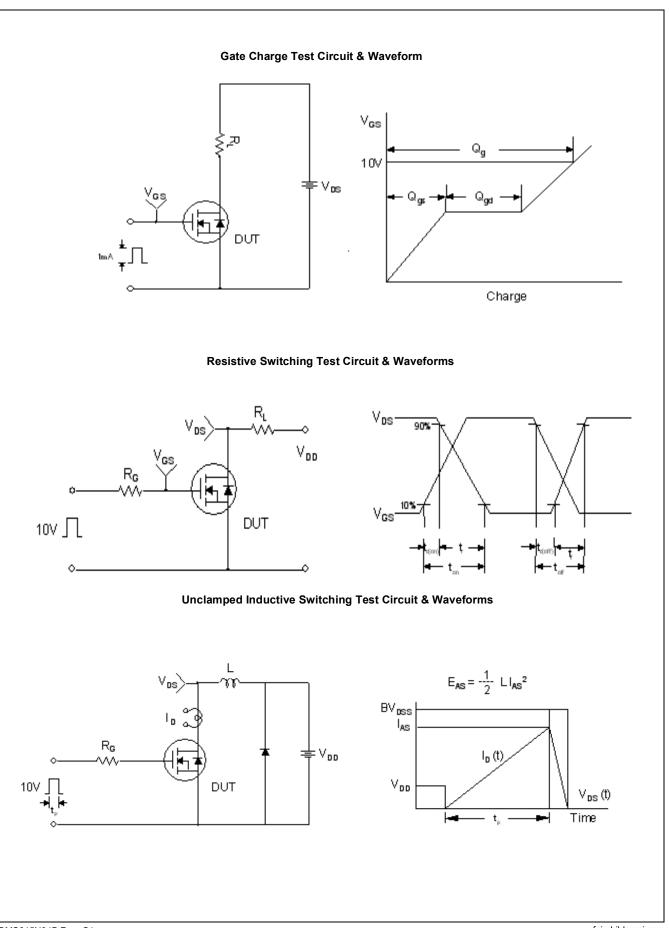
1.2



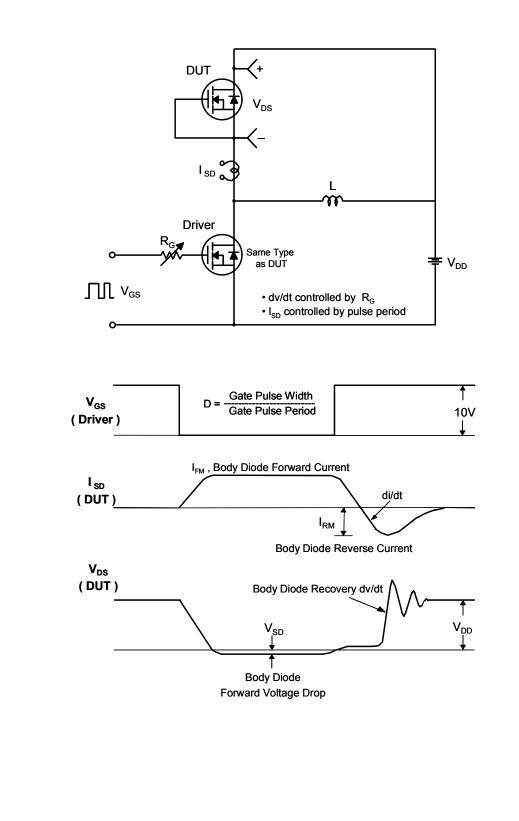
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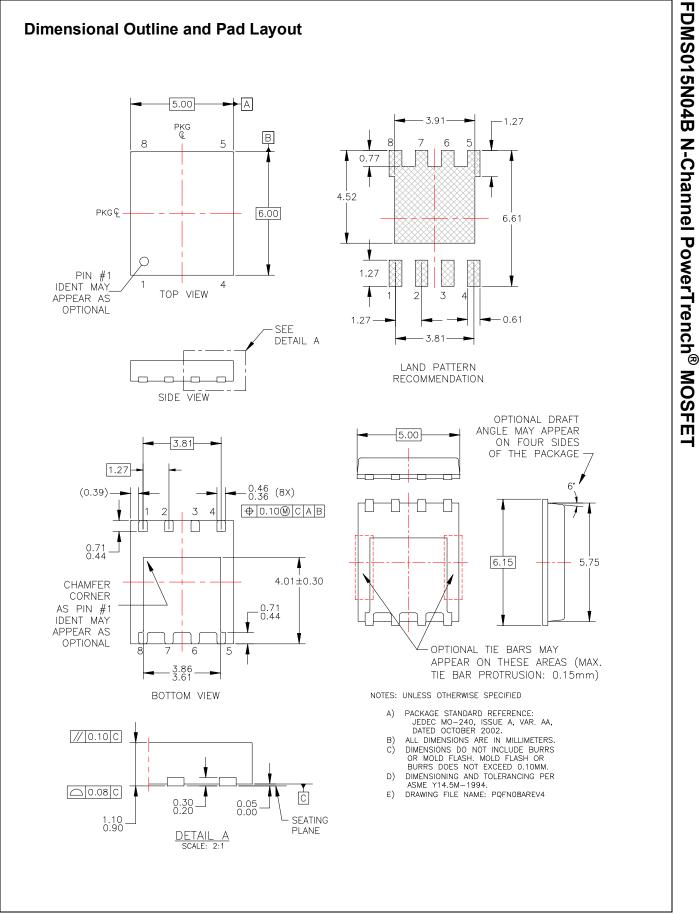






Peak Diode Recovery dv/dt Test Circuit & Waveforms









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